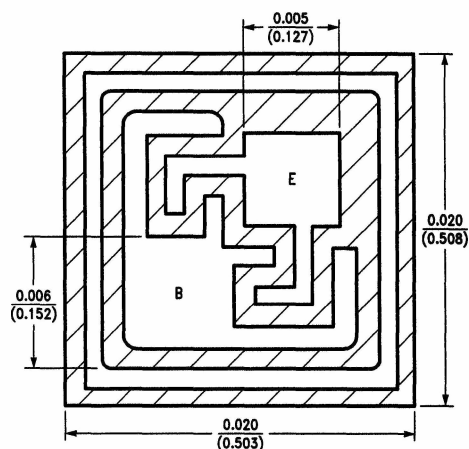




TL/G/10034-65

DESCRIPTION

Process 10 is a non-overlay, double-diffused, silicon epitaxial device. Complement to Process 68.

APPLICATION

This device was designed for general purpose amplifier applications at collector currents to 500 mA.

PRINCIPAL DEVICE TYPES

TO-92 EBC: PN100, PN2222

TO-92 ECB: 2N3415

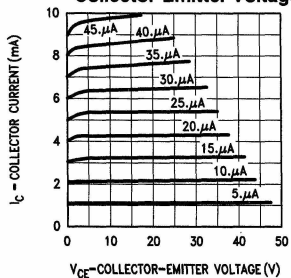
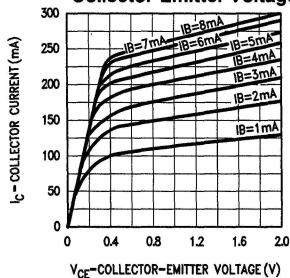
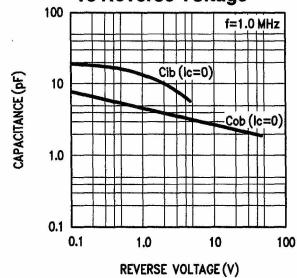
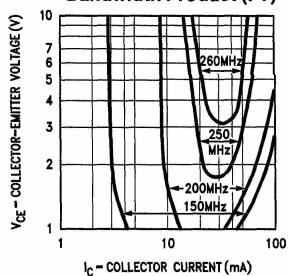
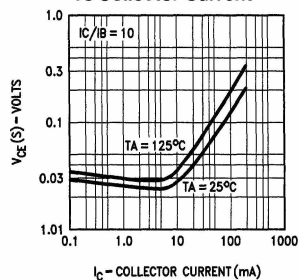
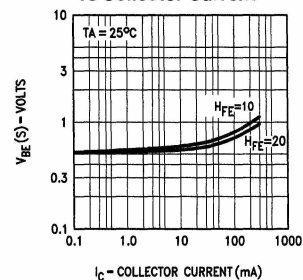
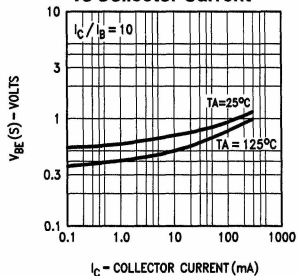
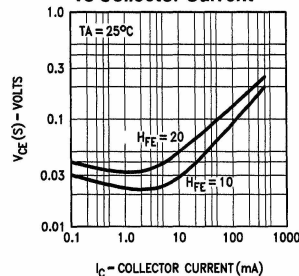
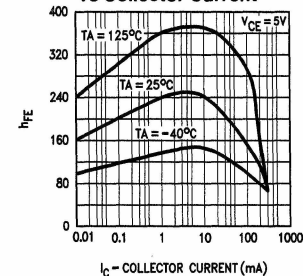
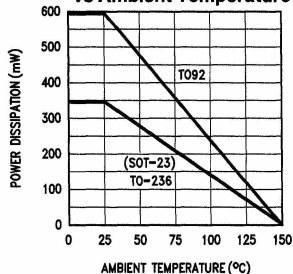
TO-116: MPQ100

TO-236: MMBT100, 100A

16-SOIC: MMPQ100

ELECTRICAL CHARACTERISTICS ($T_A = 25^\circ\text{C}$)

Symbol	Conditions	Min	Typ	Max	Units
BV_{CBO}	$I_C = 10 \mu\text{A}$	75			V
BV_{CEO}	$I_C = 1 \text{ mA}$	45			V
BV_{EBO}	$I_E = 10 \mu\text{A}$	6			V
I_{CBO}	$V_{CB} = 60\text{V}$			50	nA
I_{CES}	$V_{CE} = 40\text{V}$			50	nA
I_{EBO}	$V_{EB} = 4\text{V}$			50	nA
h_{FE}	$I_C = 100 \mu\text{A}, V_{CE} = 1\text{V}$ $I_C = 10 \text{ mA}, V_{CE} = 1\text{V}$ $I_C = 100 \text{ mA}, V_{CE} = 1\text{V}$ $I_C = 150 \text{ mA}, V_{CE} = 5\text{V}$ $I_C = 300 \text{ mA}, V_{CE} = 5\text{V}$	80 100 100 100 60	250	600	
$V_{CE(s)}$	$I_C = 10 \text{ mA}, I_B = 1 \text{ mA}$			0.2	V
$V_{BE(s)}$	$I_C = 10 \text{ mA}, I_B = 1 \text{ mA}$			0.85	V
$V_{CE(s)}$	$I_C = 200 \text{ mA}, I_B = 20 \text{ mA}$			0.4	V
$V_{BE(s)}$	$I_C = 200 \text{ mA}, I_B = 20 \text{ mA}$			1.0	V
C_{ob}	$V_{CB} = 5\text{V}, f = 1 \text{ MHz}$		3.5	4.5	pF
f_T	$V_{CE} = 20\text{V}, I_C = 20 \text{ mA}$	200	300		MHz
t_s	$I_C = 10 \text{ mA}, I_{B1} = I_{B2} = 1 \text{ mA}$		275		ns
t_{OFF}	$I_C = 150 \text{ mA}, I_{B1} = I_{B2} = 15 \text{ mA}$		225		ns
NF	$I_C = 100 \mu\text{A}, V_{CE} = 5\text{V}, R_G = 2 \text{ k}\Omega, f = 1 \text{ kHz}$		1.5		dB
$P_{D(max)}$ TO-92 TO-236	$T_A = 25^\circ\text{C}$ $T_C = 25^\circ\text{C}$	600 350			mW mW

Collector Current vs
Collector-Emitter VoltageCollector Current vs
Collector-Emitter VoltageInput and Output Capacitance
vs Reverse VoltageContours of Constant Gain
Bandwidth Product (FT)Collector Saturation Voltage
vs Collector CurrentBase Saturation Voltage
vs Collector CurrentBase Saturation Voltage
vs Collector CurrentCollector Saturation Voltage
vs Collector CurrentD.C. Current Gain
vs Collector CurrentTotal Power Dissipation
vs Ambient TemperatureSwitching Times
vs Collector Current